National Semiconductor

January 1988

MM54HC139/MM74HC139
Dual 2-To-4 Line Decoder

General Description

This decoder utilizes advanced silicon-gate CMOS technology, and is well suited to memory address decoding or data routing applications. It possesses the high noise immunity and low power consumption usually associated with CMOS circuitry, yet has speeds comparable to low power Schottky TTL logic.

The MM54HC139/MM74HC139 contain two independent one-of-four decoders each with a single active low enable input (G1, or G2). Data on the select inputs (A1, and B1 or A2, and B2) cause one of the four normally high outputs to go low.

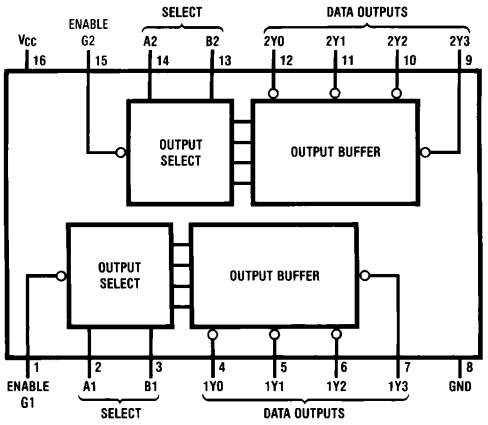
The decoder's outputs can drive 10 low power Schottky TTL equivalent loads, and are functionally as well as pin equivalent to the 54LS139/74LS139. All inputs are protected from damage due to static discharge by diodes to V_{CC} and ground.

Features

- Typical propagation delays —
  Select to outputs (4 delays): 18 ns
  Select to output (5 delays): 28 ns
  Enable to output: 20 ns
- Low power: 40 μW quiescent supply power
- Fanout of 10 LS-TTL devices
- Input current maximum 1 μA, typical 10 pA

Connection Diagram

Dual-In-Line Package



TL/F/5311–1

Order Number MM54HC139 or MM74HC139

Truth Table

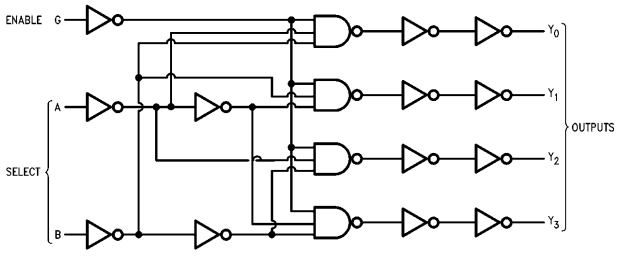
'HC139

Inputs			Outputs			
Enable	Select					
G	B	A	Y0	Y1	Y2	Y3
H	X	X	H	H	H	H
L	L	L	L	H	H	H
L	L	H	H	L	H	H
L	H	L	H	H	L	H
L	H	H	H	H	H	L

H = high level, L = low level, X = don't care

Logic Diagram

MM54HC139/MM74HC139



TL/F/5311–2

(1 of 2)

RRD-B30M105/Printed in U. S. A.

Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V_{CC})	−0.5 to +7.0V
DC Input Voltage (V_{IN})	−1.5 to V_{CC} +1.5V
DC Output Voltage (V_{OUT})	−0.5 to V_{CC} +0.5V
Clamp Diode Current (I_{IK}, I_{OK})	±20 mA
DC Output Current, per pin (I_{OUT})	±25 mA
DC V_{CC} or GND Current, per pin (I_{CC})	±50 mA
Storage Temperature Range (T_{STG})	−65°C to +150°C
Power Dissipation (P_D) (Note 3)	600 mW
S.O. Package only	500 mW
Lead Temp. (T_L) (Soldering 10 seconds)	260°C

Operating Conditions

		Min	Max	Units
Supply Voltage (V_{CC})		2	6	V
DC Input or Output Voltage (V_{IN}, V_{OUT})		0	V_{CC}	V
Operating Temp. Range (T_A)				
MM74HC		−40	+85	°C
MM54HC		−55	+125	°C
Input Rise or Fall Times (t_r, t_f)	V_{CC} = 2.0V		1000	ns
	V_{CC} = 4.5V		500	ns
	V_{CC} = 6.0V		400	ns

DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	V_{CC}	T_A = 25°C	74HC T_A = −40 to 85°C	54HC T_A = −55 to 125°C	Units
				Typ	Guaranteed Limits		
V_{IH}	Minimum High Level Input Voltage		2.0V		1.5	1.5	V
			4.5V		3.15	3.15	V
			6.0V		4.2	4.2	V
V_{IL}	Maximum Low Level Input Voltage**		2.0V		0.5	0.5	V
			4.5V		1.35	1.35	V
			6.0V		1.8	1.8	V
V_{OH}	Minimum High Level Output Voltage	V_{IN} = V_{IH} or V_{IL} $\|I_{OUT}\| \le 20\ \mu A$	2.0V	2.0	1.9	1.9	V
			4.5V	4.5	4.4	4.4	V
			6.0V	6.0	5.9	5.9	V
		V_{IN} = V_{IH} or V_{IL} $\|I_{OUT}\| \le 4.0$ mA	4.5V	4.2	3.98	3.84	3.7	V
		$\|I_{OUT}\| \le 5.2$ mA	6.0V	5.7	5.48	5.34	5.2	V
V_{OL}	Maximum Low Level Output Voltage	V_{IN} = V_{IH} or V_{IL} $\|I_{OUT}\| \le 20\ \mu A$	2.0V	0	0.1	0.1	0.1	V
			4.5V	0	0.1	0.1	0.1	V
			6.0V	0	0.1	0.1	0.1	V
		V_{IN} = V_{IH} or V_{IL} $\|I_{OUT}\| \le 4.0$ mA	4.5V	0.2	0.26	0.33	0.4	V
		$\|I_{OUT}\| \le 5.2$ mA	6.0V	0.2	0.26	0.33	0.4	V
I_{IN}	Maximum Input Current	V_{IN} = V_{CC} or GND	6.0V		±0.1	±1.0	±1.0	μA
I_{CC}	Maximum Quiescent Supply Current	V_{IN} = V_{CC} or GND I_{OUT} = 0 μA	6.0V		8.0	80	160	μA

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: −12 mW/°C from 65°C to 85°C; ceramic "J" package: −12 mW/°C from 100°C to 125°C.

Note 4: For a power supply of 5V ±10% the worst case output voltages (V_{OH}, and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at V_{CC} = 5.5V and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN}, I_{CC}, and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

**V_{IL} limits are currently tested at 20% of V_{CC}. The above V_{IL} specification (30% of V_{CC}) will be implemented no later than Q1, CY'89.

AC Electrical Characteristics

$V_{CC} = 5V$, $T_A = 25°C$, $C_L = 15$ pF, $t_r = t_f = 6$ ns

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
t_{PHL}, t_{PLH}	Maximum Propagation Delay, Binary Select to any Output 4 levels of delay		18	30	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay, Binary Select to any Output 5 levels of delay		28	38	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay, Enable to any Output		19	30	ns

AC Electrical Characteristics $C_L = 50$ pF, $t_r = t_f = 6$ ns (unless otherwise specified)

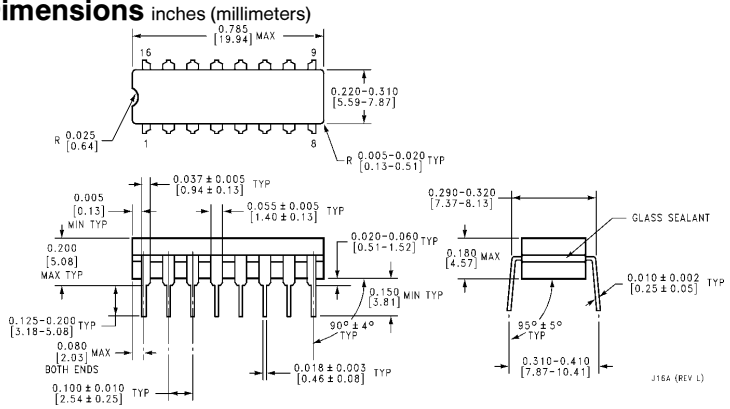
Symbol	Parameter	Conditions	V_{CC}	$T_A = 25°C$		74HC $T_A = -40$ to $85°C$	54HC $T_A = -55$ to $125°C$	Units
				Typ	Guaranteed Limits			
t_{PHL}, t_{PLH}	Maximum Propagation Delay Binary Select to any Output 4 levels of delay	(Note 6)	2.0V	110	175	219	254	ns
			4.5V	22	35	44	51	ns
			6.0V	18	30	38	44	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay Binary Select to any Output 5 levels of delay	(Note 7)	2.0V	165	220	275	320	ns
			4.5V	33	44	55	64	ns
			6.0V	28	38	47	54	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay Enable to any Output		2.0V	115	175	219	254	ns
			4.5V	23	35	44	51	ns
			6.0V	19	30	38	44	ns
t_{TLH}, t_{TLH}	Maximum Output Rise and Fall Time		2.0V	30	75	95	110	ns
			4.5V	8	15	19	22	ns
			6.0V	7	13	16	19	ns
C_{IN}	Maximum Input Capacitance			3	10	10	10	pF
C_{PD}	Power Dissipation Capacitance (Note 5)	(Note 5)		75				pF

Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} V_{CC} f + I_{CC}$.

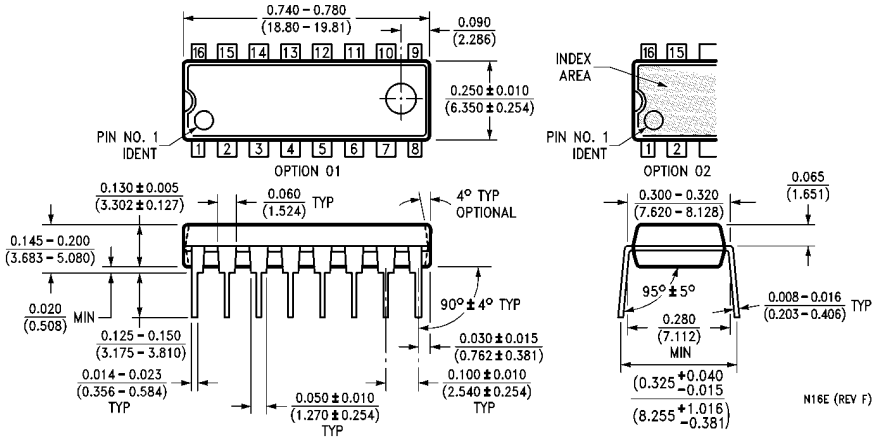
Note 6: 4 levels of delay are A to Y1, Y3 and B to Y2, Y3.

Note 7: 5 levels of delay are A to Y0, Y2 and B to Y0, Y1.

Physical Dimensions inches (millimeters)



Order Number MM54HC139J or MM74HC139J
NS Package J16A



Order Number MM74HC139N
NS Package N16E

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